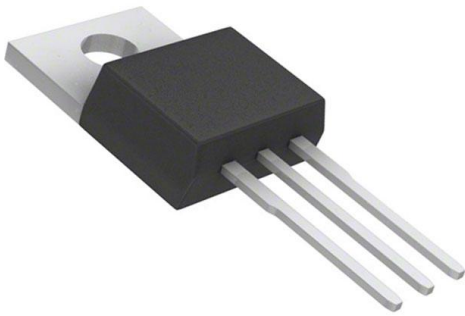


PSMN013-100PS,127 Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	PSMN013-100PS,127-DG
Manufacturer	Nexperia USA Inc.
Manufacturer Product Number	PSMN013-100PS,127
Description	MOSFET N-CH 100V 68A TO220AB
Detailed Description	N-Channel 100 V 68A (Tc) 170W (Tc) Through Hole TO-220AB



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

PSMN013-100PS,127

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

100 V

Drive Voltage (Max Rds On, Min Rds On):

10V

Vgs(th) (Max) @ Id:

4V @ 1mA

Vgs (Max):

±20V

FET Feature:

-

Operating Temperature:

-55°C ~ 175°C (Tj)

Supplier Device Package:

TO-220AB

Base Product Number:

PSMN013

Manufacturer:

Nexperia USA Inc.

Product Status:

Obsolete

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

68A (Tc)

Rds On (Max) @ Id, Vgs:

13.9mOhm @ 15A, 10V

Gate Charge (Qg) (Max) @ Vgs:

59 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

3195 pF @ 50 V

Power Dissipation (Max):

170W (Tc)

Mounting Type:

Through Hole

Package / Case:

TO-220-3

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



PSMN013-100PS

N-channel 100V 13.9mΩ standard level MOSFET in TO220.

10 August 2012

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Improved dynamic avalanche performance
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$		-	-	100	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; Fig. 1	[1]	-	-	68	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 2		-	-	170	W
T_j	junction temperature			-55	-	175	°C
Static characteristics							
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 15\text{ A}$; $T_j = 100\text{ °C}$; Fig. 12		-	19.4	25	mΩ
		$V_{GS} = 10\text{ V}$; $I_D = 15\text{ A}$; $T_j = 25\text{ °C}$; Fig. 13	[2]	-	10.8	13.9	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $V_{DS} = 50\text{ V}$; Fig. 15 ; Fig. 14		-	17	-	nC

N-channel 100V 13.9m Ω standard level MOSFET in TO220.

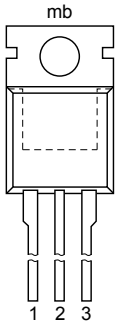
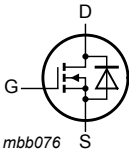
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$Q_{G(\text{tot})}$	total gate charge	$V_{GS} = 10 \text{ V}$; $I_D = 25 \text{ A}$; $V_{DS} = 50 \text{ V}$; Fig. 14 ; Fig. 15	-	59	-	nC
Avalanche ruggedness						
$E_{DS(\text{AL})S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}$; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$; $I_D = 68 \text{ A}$; $V_{\text{sup}} \leq 100 \text{ V}$; unclamped; $R_{GS} = 50 \text{ } \Omega$	-	-	128	mJ

[1] Continuous current is limited by package

[2] Measured 3 mm from package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>TO-220AB (SOT78)</p>	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN013-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN013-100PS	PSMN013-100PS

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$		-	100	V
V_{DGR}	drain-gate voltage	$T_j \leq 175\text{ °C}; T_j \geq 25\text{ °C}; R_{GS} = 20\text{ k}\Omega$		-	100	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 100\text{ °C}; \text{Fig. 1}$	[1]	-	47	A
		$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}; \text{Fig. 1}$	[1]	-	68	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}; T_{mb} = 25\text{ °C}; \text{Fig. 3}$		-	272	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}; \text{Fig. 2}$		-	170	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ °C}$	[1]	-	68	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}; T_{mb} = 25\text{ °C}$		-	272	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C}; I_D = 68\text{ A}; V_{sup} \leq 100\text{ V}; \text{unclamped}; R_{GS} = 50\text{ }\Omega$		-	128	mJ

[1] Continuous current is limited by package

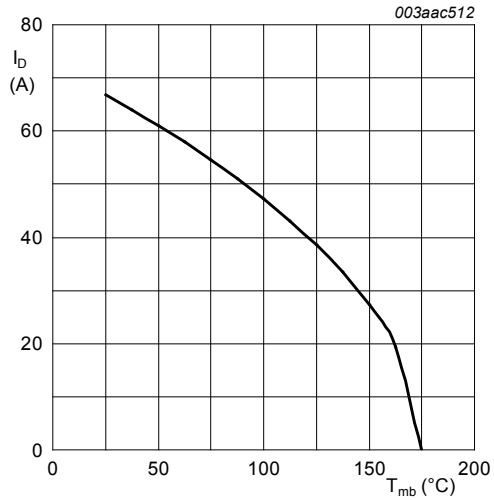


Fig. 1. Continuous drain current as a function of mounting base temperature

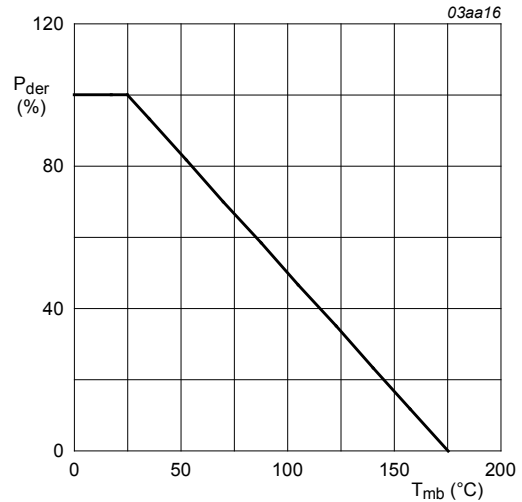


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

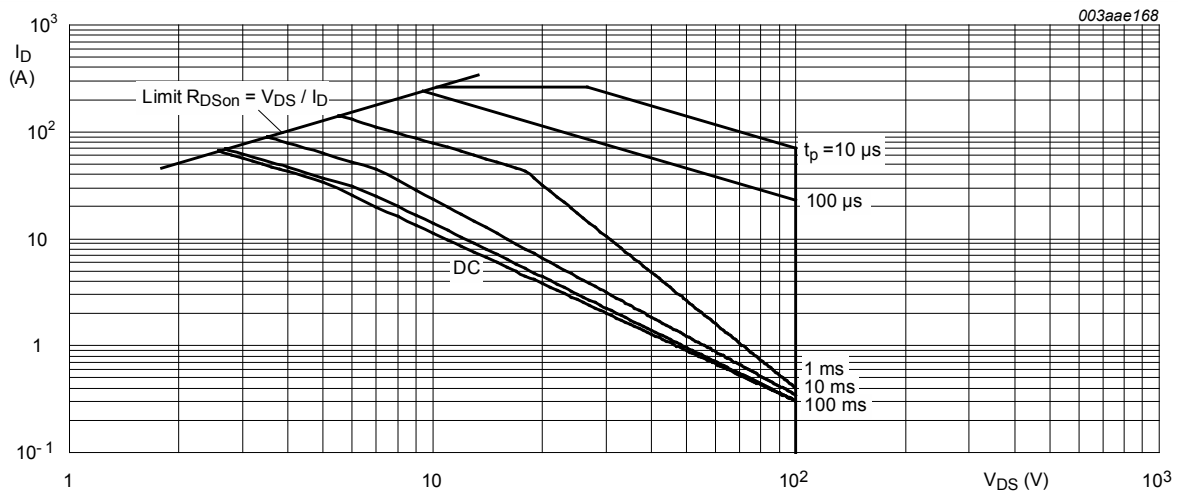


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

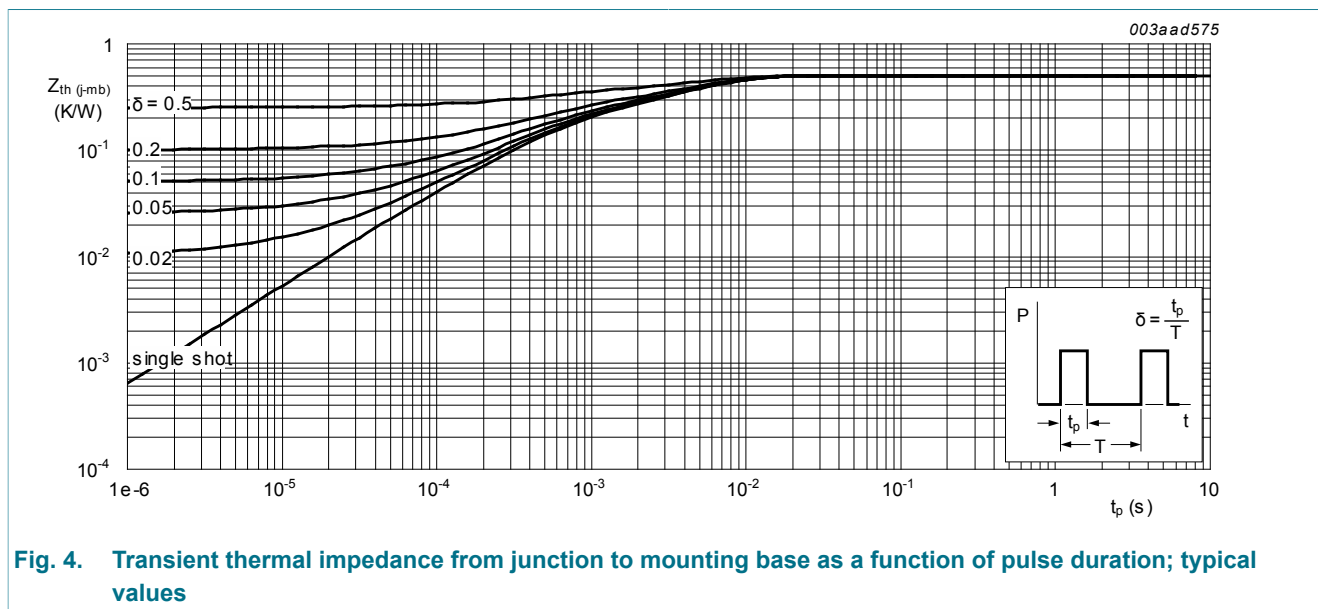
$$T_{mb} = 25^{\circ}\text{C}; I_{DM} \text{ is a single pulse}$$

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	0.5	0.9	K/W

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	90	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ Fig. 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ Fig. 10; Fig. 11	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ Fig. 10	-	-	4.6	V
I_{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$	-	-	100	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.06	2	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ }^\circ\text{C};$ Fig. 12	-	19.4	25	mΩ

N-channel 100V 13.9mΩ standard level MOSFET in TO220.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_{GS} = 10\text{ V}$; $I_D = 15\text{ A}$; $T_j = 175\text{ °C}$; Fig. 12	-	29.5	38.9	mΩ
		$V_{GS} = 10\text{ V}$; $I_D = 15\text{ A}$; $T_j = 25\text{ °C}$; Fig. 13	[1]	10.8	13.9	mΩ
R_G	internal gate resistance (AC)	$f = 1\text{ MHz}$	-	1	-	Ω
Dynamic characteristics						
$Q_{G(\text{tot})}$	total gate charge	$I_D = 25\text{ A}$; $V_{DS} = 50\text{ V}$; $V_{GS} = 10\text{ V}$; Fig. 14 ; Fig. 15	-	59	-	nC
		$I_D = 0\text{ A}$; $V_{DS} = 0\text{ V}$; $V_{GS} = 10\text{ V}$	-	47.6	-	nC
Q_{GS}	gate-source charge	$I_D = 25\text{ A}$; $V_{DS} = 50\text{ V}$; $V_{GS} = 10\text{ V}$; Fig. 14 ; Fig. 15	-	13.8	-	nC
$Q_{GS(\text{th})}$	pre-threshold gate-source charge	$I_D = 25\text{ A}$; $V_{DS} = 50\text{ V}$; $V_{GS} = 10\text{ V}$; Fig. 15	-	9.2	-	nC
$Q_{GS(\text{th-pl})}$	post-threshold gate-source charge		-	4.6	-	nC
Q_{GD}	gate-drain charge	$I_D = 25\text{ A}$; $V_{DS} = 50\text{ V}$; $V_{GS} = 10\text{ V}$; Fig. 15 ; Fig. 14	-	17	-	nC
$V_{GS(\text{pl})}$	gate-source plateau voltage	$V_{DS} = 50\text{ V}$; Fig. 15 ; Fig. 14	-	4.4	-	V
C_{iss}	input capacitance	$V_{DS} = 50\text{ V}$; $V_{GS} = 0\text{ V}$; $f = 1\text{ MHz}$; $T_j = 25\text{ °C}$; Fig. 16	-	3195	-	pF
C_{oss}	output capacitance		-	221	-	pF
C_{rss}	reverse transfer capacitance		-	136	-	pF
$t_{d(\text{on})}$	turn-on delay time	$V_{DS} = 50\text{ V}$; $R_L = 2\text{ Ω}$; $V_{GS} = 10\text{ V}$; $R_{G(\text{ext})} = 4.7\text{ Ω}$; $T_j = 25\text{ °C}$	-	20.7	-	ns
t_r	rise time		-	25	-	ns
$t_{d(\text{off})}$	turn-off delay time		-	52.5	-	ns
t_f	fall time		-	24	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 15\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ °C}$; Fig. 17	-	0.85	1.2	V
t_{rr}	reverse recovery time	$I_S = 25\text{ A}$; $di_S/dt = 100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 50\text{ V}$	-	52	-	ns
Q_r	recovered charge		-	109	-	nC

[1] Measured 3 mm from package.

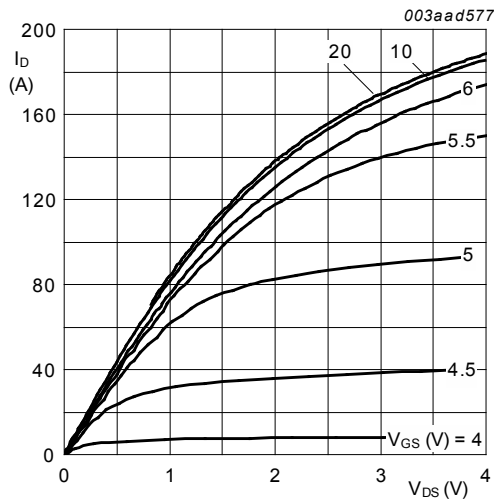


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25^\circ\text{C}$$

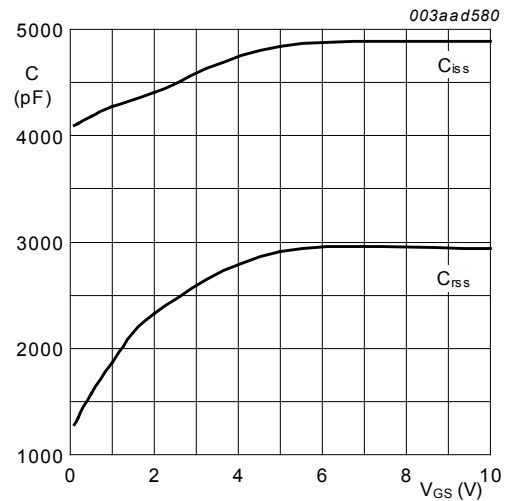


Fig. 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

$$V_{DS} = 0\text{V}; f = 1\text{MHz}$$

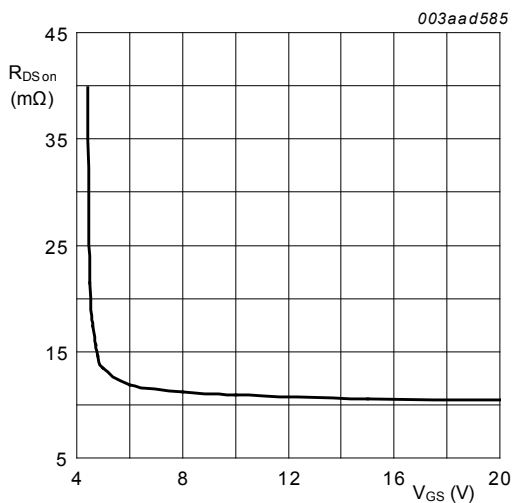


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^\circ\text{C}$$

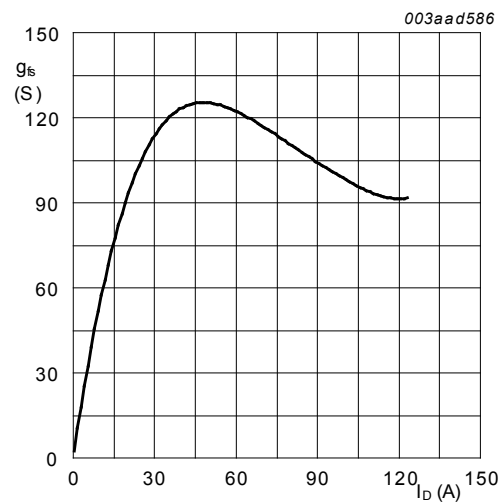


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j = 25^\circ\text{C}; V_{DS} = 15\text{V}$$

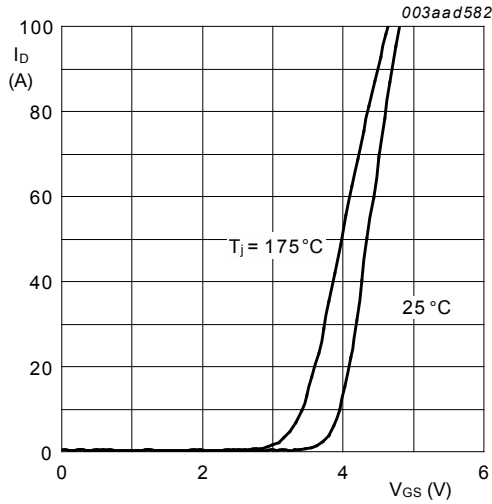


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} > I_D \times R_{DSon}$$

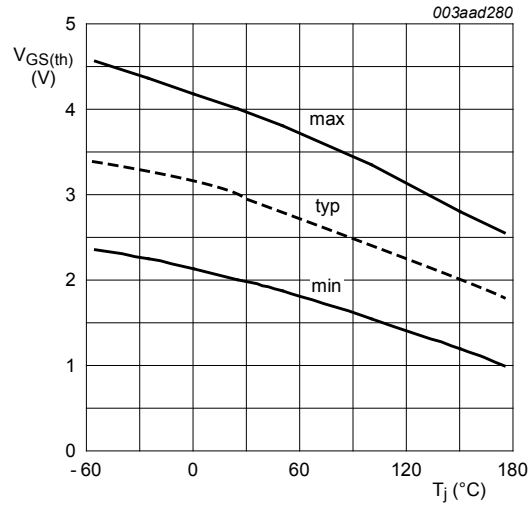


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

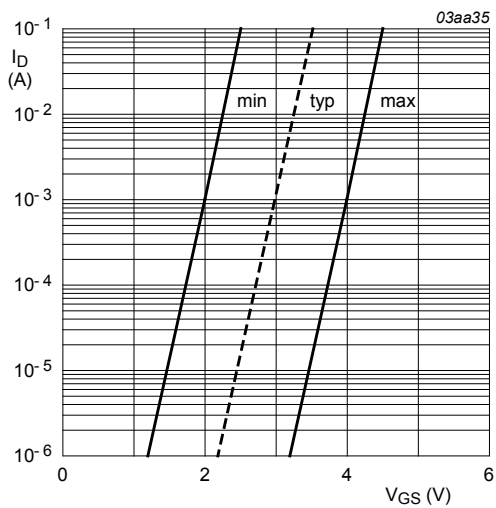


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$$

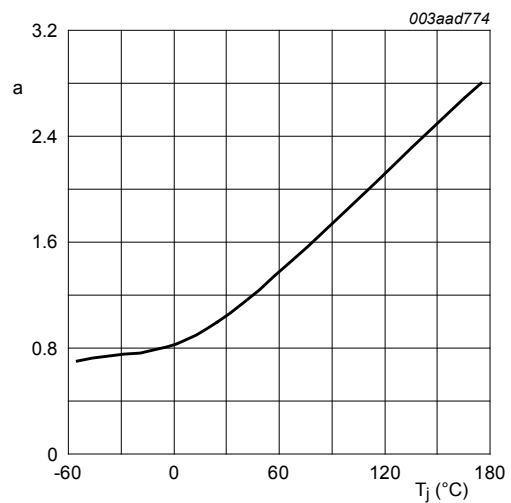


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

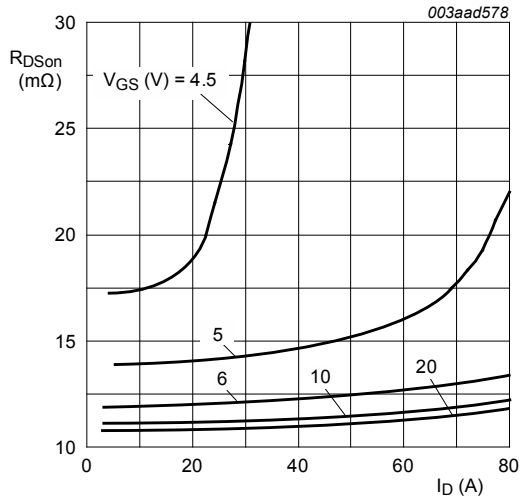


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25^\circ\text{C}$

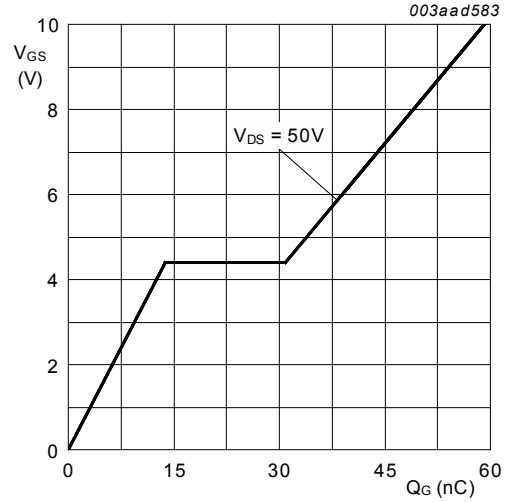


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^\circ\text{C}; I_D = 25$ A

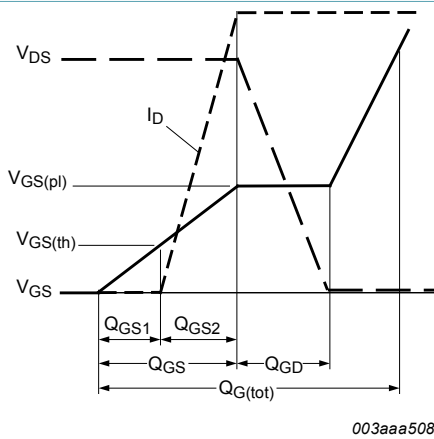


Fig. 15. Gate charge waveform definitions

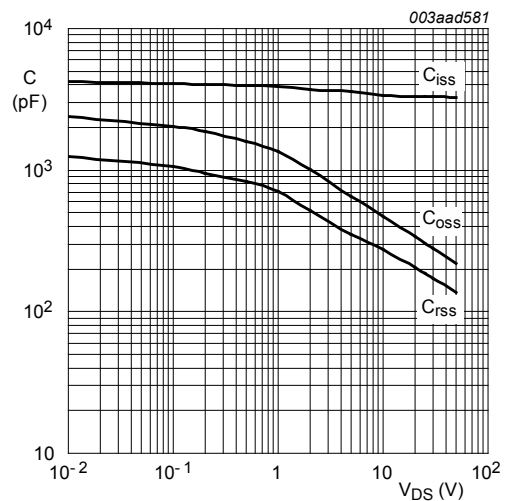


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0$ V; $f = 1$ MHz

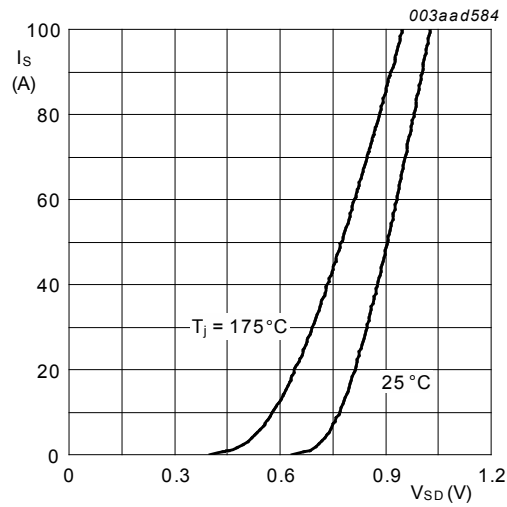


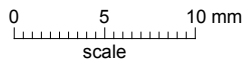
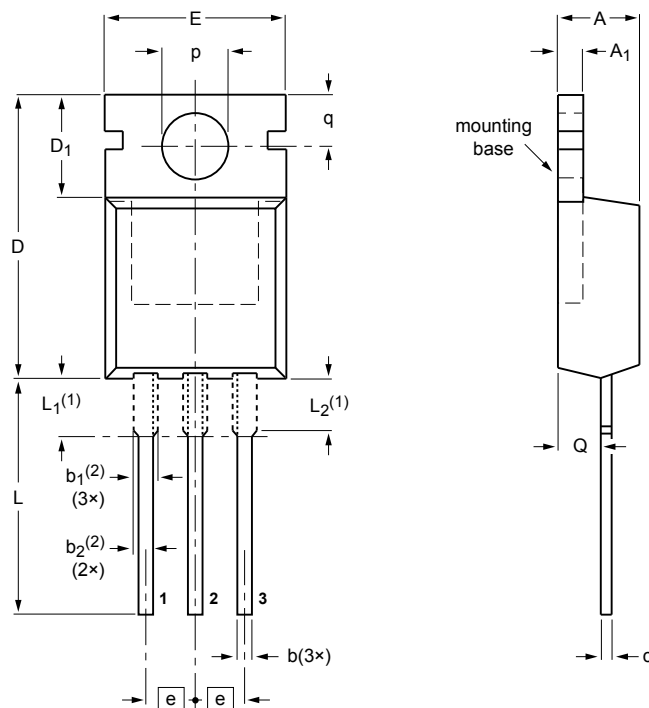
Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

8. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (2)	b ₂ (2)	c	D	D ₁	E	e	L	L ₁ (1)	L ₂ (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- Lead shoulder designs may vary.
- Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig. 18. TO-220AB (SOT78)

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nexperia.com>.

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10. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	3
6	Thermal characteristics	4
7	Characteristics	5
8	Package outline	11
9	Legal information	12
9.1	Data sheet status	12
9.2	Definitions	12
9.3	Disclaimers	12
9.4	Trademarks	13

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